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DESIGN AND ANALYSIS OF POWER EFFICIENT SENSE AMPLIFIER BASED FLIP FLOP

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ABSTRACT: - In digital VLSI system the clock distribution network and flip flops are most power consuming components. The reduction of power consumption by clock distribution networks & flip flop makes the total VLSI system as low power VLSI system. In the earlier VLSI system design, different power consumption methods are followed to design the various flip-flops. The SABFF (sense amplifier based flip flop) is one of the types of flip flops in digital VLSI system. The SABFF consists of pulse generator, sensing stage (frontend), latching stage (backend). In previous sense amplifier based flip flops, the sensing stage (frontend) is focused more to make the flip flop as low power consuming element. The proposed work is to design power efficient sense amplifier based flip flop by focusing the sensing stage. The various analyses on the sense amplifier based flip flop is carried out by changing the different sensing stages such as Current mirror sense amplifier (Ct mirror), Full latch sense amplifier.

Keywords: SABFF (sense amplifier based flip-flop) Ct mirror (current mirror)

INTRODUCTION

Integrated circuits were made possible by experimental discoveries which showed that semiconductor devices could perform the functions of vacuum tubes, and by mid-20th-century technology advancements in semiconductor device fabrication. The integration of large numbers of tiny transistors into a small chip was an enormous improvement over the manual assembly of circuits using discrete electronic components. The integrated circuits mass production capability, reliability, and building-block approach to circuit design ensured the rapid adoption of standardized ICs in place of designs using discrete transistors. There are two main advantages of ICs over discrete circuits - cost and performance. Cost is low because the chips, with all their components, are printed as a unit by photolithography and not constructed a transistor at a time. Performance is high since the components switch quickly and consume little power, because the components are small and close together. As of 2006, chip areas range from a few square mm to around 250 mm², with up to 1 million transistors per mm².

IC design productivity depends on the efficiency with which the design may be converted from concept to architecture, to logic and memory, to circuit and hence to a physical layout.

In many digital very large scale integration (VLSI) designs, the clock system that includes clock distribution network and flip-flops, is one of the most power consumption components. It accounts for 30% to 60% of the total system power, where 90% of which is consumed by the flip-flops and the last branches of the clock distribution network that is driving the flip-flop. With the recent trend in frequency scaling and deep pipelining, this clocking system power may be even more pronounced. As the power budget of today's portable digital circuit is severely limited, it is important to reduce the power dissipation in both clock distribution networks and flip-flops. Moreover, because of the tight timing budget at high frequency operation, the latency of the flip-flops should be minimized. Hence, the ability to achieve a design that ensures both power consumption and small latency is essential in modern VLSI technology. The dual-edge triggering is an important technique to reduce the power consumption in the clock distribution network.

Dual Edge Triggering

By utilizing dual-edge triggering, the flip-flop is capable of sampling data on both rising and falling edges of the clock so that only half the clock frequency is needed to obtain the same data throughput of single edge-triggered flip-flops (SETFFs). Recently, several low-power high-speed DETFF structures have been proposed. In this work, we extensively studied the operation of existing flip-flop architectures, analysed their weaknesses and proposed new sense-amplifier based flip-flop circuits (here in after, referred to as a "SAFF" circuit) due to its differential characteristics, fast operation speed, and low-power consumption. This SAFF circuit is implemented by various approaches within digital circuits such as microprocessors, digital signal processing units, and the like. The first flip-flop achieves substantial power reduction by concurrently incorporating dual-edge triggering and conditional pre charging. It also minimizes the latency by making use of a fast symmetrical latch. By using the first proposed design as the baseline circuit, a novel clock gating flip-flop circuit is developed to further reduce the power dissipation and at low input switching activity, the second proposed design promises an even greater amount of power savings.

SENSE AMPLIFIER

Sense Amplifier is important component of memory design. The choice and design of Sense Amplifier robustness of bit line sensing impacting read speed and power. Due to variety of Sense Amplifiers in semiconductor memories and the impact they have on final specs of memory, the sense amplifiers have become a separate class of circuit. Sense amplifiers play a major role in the functionality Performance and reliability of memory circuits. Sense amplifier performs a function like amplification, power reduction & delay reduction

In this paper a new method for power reduction by clock distribution networks & flip flop has been proposed and developed which makes the total VLSI system as low power VLSI system.

This paper has been implemented in low power application in VLSI system to design a flip-flop.

SURVEY OF EXISTING METHODS

LOW-POWER CMOS DESIGN FOR LOW-SWING CIRCUITS

This paper describes some of the circuit level techniques for low-power CMOS designs. VTH control circuits are necessary for achieving low-threshold voltage in high-speed low-voltage applications. In order to reduce the clock system power, it is effective to reduce a clock voltage swing. Such idea is embodied in the Reduced Clock Swing Flip-Flop (RCSFF).

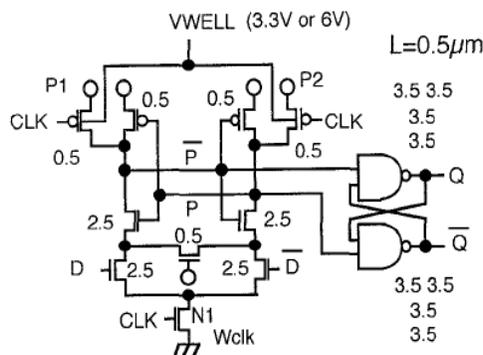


Figure 2.1 Reduced Clock Swing Flip Flop

The RCSFF is composed of a current-latch sense amplifier and cross-coupled NAND gates which act as a slave latch. This type of flip-flop was first introduced in 1994 and it is extensively used in a microprocessor design. The sense-amplifying FE is often used with low-swing circuits because there is no DC leakage path even if the input is not full swing being different from the conventional gates or F/F's. The salient feature of the RCSFF is to accept a reduced voltage swing clock. The voltage swing, V_{clk} , can be as low as 1V.

LOW-ENERGY FLIP-FLOPS- A COMPARITIVE STUDY

This paper develops a methodology for selecting and optimizing flip-flops for low-energy systems with constant throughput. Characterization metrics, relevant to low-energy systems are discussed, providing insight into timing and energy parameters at both the circuit and system levels. Transistor sizes are optimized for minimal delay under constrained energy consumption. This methodology is applied to characterization of various flip-flop styles and their comparison in 0.25µm CMOS technology under scaled supply voltages.

A transmission-gate master-slave latch pair has the largest internal race margin, lowest energy consumption, and has energy-delay product comparable to much faster pulse-triggered latches. A common design approach for minimizing energy consumption in flip-flops is to reduce the switching component of Energy, $E = a \cdot C_{sw} \cdot V_{swing} \cdot V_{..}$

Based on this formula, energy consumption can be reduced by simply minimizing each of the terms in the product expression. However, lowering the supply voltage results in increased flip-flop delay, so the delay has to be included in the optimization metric. Clocked capacitances should be minimized in order to reduce the clock load. The total circuit area depends on the size of the output load and required driving strength. With energy reduction in clocked nodes and the output load, sizing for optimal performance under these energy constraints reduces to optimizing the speed of the flip-flop's critical path. This closely approximates the sizing for optimal energy-delay product (EDP). The circuit is optimized to drive an output load of 4 standard loads (SL), where SL is the input capacitance of a unity buffer from standard cell library. While 4SL load is most common effective fan out in synthesized low energy systems, sizing procedure can be extended to any load. The method of logical effort is used in transistor size optimization.

It quantifies the driving capability of a logic gate relative to a standard inverter so that a valid correlation can be established between the required transistor sizes and the computed logical effort. In this example, only the Clk-Q delay is optimized. The path in the TGFF is responsible for the Clk-Q delay. The off-path capacitance, $C_{offpath}$, equal to the gate capacitance of two minimum width feedback transistors. Keeper transistors in the feedback of both master and slave latches are minimal width. Minimum sizing of the master stage minimizes the energy consumption with little impact on the setup time.

CURRENT MIRROR SENSE AMPLIFIER

This paper describes that current mirror sense amplifier has better improvement in the noise immunity and speed of read circuit. Current Mirror Sense Amplifier takes differential input and amplify them large signal output. The differential approach presents numerous advantages over single ended counterpart – one of the most important being common mode rejection. That is such amplifier rejects the noise that is equally injected at both input. The signal common at both input suppressed at output of amplifier. The drawback is current mirror sense amplifier that it consumes more power than other type due to dc bias current.

FULL LATCH SENSE AMPLIFIER

The power problem is one of the most serious limitations in the high performance - VLSI's circuits. The power dissipation of on chip memories and interface circuits occupies a large portion of the total power dissipation. Full latch sense amplifier consumes less power than other configuration of sense amplifier. Even though the conventional latch based on two cross coupled inverters is widely used as a sense amplifier, it always requires some decoupling at its input. This drawback does not occur for the latch circuit shown in fig -3. The most critical point of latch-type sense amplifiers is that once the decision process has started, it does not recover unless the circuit is reset to the metastable. Due to fast speed, low power consumption, high input impedance and full-swing output latch type sense amplifier are very attractive for many applications.

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Based on this formula, energy consumption can be reduced by simply minimizing each of the terms in the product expression. However, lowering the supply voltage results in increased flip-flop delay, so the delay has to be included in the optimization metric. Clocked capacitances should be minimized in order to reduce the clock load. The total circuit area depends on the size of the output load and required driving strength. With energy reduction in clocked nodes and the output load, sizing for optimal performance under these energy constraints reduces to optimizing the speed of the flip-flop's critical path. This closely approximates the sizing for optimal energy-delay product (EDP). The circuit is optimized to drive an output load of 4 standard loads (SL), where SL is the input capacitance of a unity buffer from standard cell library. While 4SL load is most common effective fanout in synthesized low energy systems, sizing procedure can be extended to any load. The method of logical effort is used in transistor size optimization.

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2.5 FULL LATCH SENSE AMPLIFIER

The power problem is one of the most serious limitations in the high performance - VLSI's circuits. The power dissipation of on chip memories and interface circuits occupies a large portion of the total power dissipation. Full latch sense amplifier consumes less power than other configuration of sense amplifier. Even though the conventional latch based on two cross coupled inverters is widely used as a sense amplifier, it always requires some decoupling at its input. This drawback does not occur for the latch circuit shown in fig -3. The most critical point of latch-type sense amplifiers is that once the decision process has started, it does not recover unless the circuit is reset to the metastable. Due to fast speed, low power consumption, high input impedance and full-swing output latch type sense amplifier are very attractive for many applications.

DOUBLE-EDGE TRIGGERED FLIP-FLOP

In this paper, a new technique for implementing low-energy double-edge triggered flip-flops is introduced. The new technique employs a clock branch-sharing scheme to reduce the number of clocked transistors in the design. This design also employs conditional discharge and split-path techniques to further reduce switching activity and short-circuit currents, respectively.

As compared to the other state of the art double-edge triggered flip-flop designs, this CBS_ip design has an improvement of up to 20% and 12.4% in view of power consumption and PDP, respectively. This CBS_ip uses a clock branch sharing scheme to sample the clock transitions, which efficiently reduces the number of clocked transistors and results in lower power while maintaining a competitive speed.

It employs the conditional discharge technique and the split path technique to reduce the redundant switching activity and short circuit current, respectively. The CBS_ip flip flop has the least number of clocked transistors and lowest power; hence, it is suitable for use in high performance and low-power environments

IMPROVEDSENSE-AMPLIFIER-BASED FLIP-FLOP

Design and experimental evaluation of a new sense amplifier- based flip-flop (SAFF) is presented. It was found that the main speed bottleneck of existing SAFF's is the cross-coupled set-reset (SR) latch in the output stage. The new flip-flop uses a new output stage latch topology that significantly reduces delay and improves driving capability. The performance of this flip-flop is verified by measurements on a test chip implemented in 0.18 μm effective channel length CMOS. Demonstrated speed places it among the fastest flip-flops used in the state-of-the-art processors.

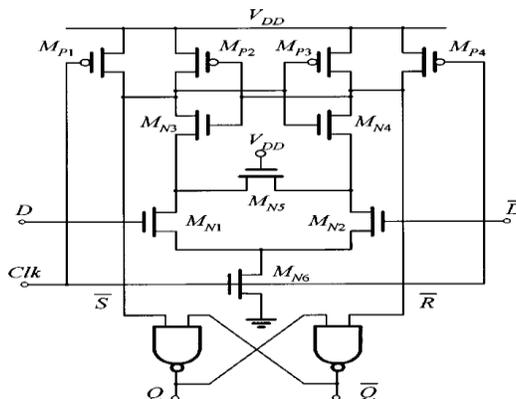


Fig. 2.2 Sense amplifier- based flip-flop (SAFF)

This allows flip-flop realization in a circuit topology yielding optimal speed and power. The strong driving capability of this flip-flop makes it suitable for GHz design characterized with a short pipeline and high fan-out. The differential input signal nature of the flip-flop makes it compatible with the logic utilizing reduced signal swing.

3.2 Adaptive Clocking Dual Edge-Triggered Sense-Amplifier Flip-Flop

The schematic diagram of adaptive clocking dual-edge triggered sense amplifier flip-flop (ACSFAFF) is presented in Fig. 3.3. ACSFAFF is an implicit dual-edge triggered sense amplifier flipflop. It consists of three stages, i.e., the adaptive clock inverting stage, the front-end sensing stage and the Nikolic's latch stage. The adaptive clock inverter chain is designed to disable some internal clocked transistors when the data switching activity is low. The signal derived from node NC of the sensing stage is used to implement adaptive clocking.

If input D is different from output Q, node NC will be pulled up, to turn on transistors N1 and N2. Consequently, the desired inverted and delayed signals, CLK3 and CLK4, will be produced so that a narrow transparent window is created on the rising or falling edges of the clock. Either SB or RB will be discharged during this transparent period, changing the output state in the latching stage. Once the output state is altered, the charging path of NC is blocked and NC will be discharged through either N3 and N4 or N5 and N6, thereby disabling the inverter chain.

When D is the same as Q, node NC is low and the flip-flop is opaque. ACSFAFF obtains great power reduction at low switching activity. Nevertheless, the adaptive clocking requires more transistors and hence causing the circuit to be more complex. This will lead to greater power consumption at high switching activity and the degradation of the flip-flop speed. Since the front-end sensing stage of ACSFAFF is a differential pair like the sense-amplifier, the ratio of the desired differential-mode gain to the undesired common mode gain is analysed. The magnitude of this ratio is defined as the common mode rejection ratio (CMRR). CMRR serves as a measure of the amount of wanted signal to the unwanted corruption that appears at the output when the input contains both the differential component and common mode noise.

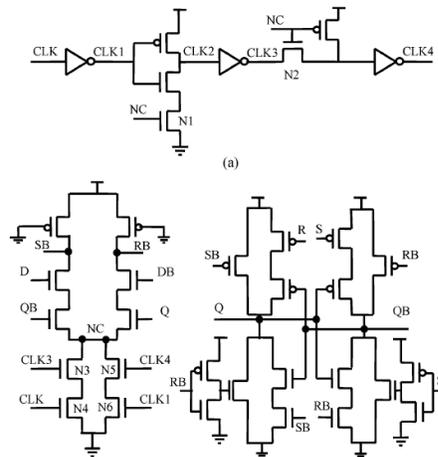
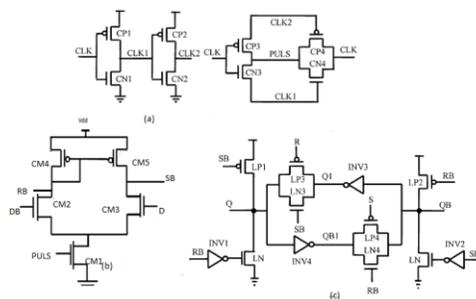


Fig. 3.1 Adaptive clocking dual edge-triggered sense-amplifier flip-flop: (a) Adaptive clocking inverter chain; (b) Front end sensing stage; and (c) Nikolic's latch.

The CMRR of ACSFAFF is the same as that of conventional differential amplifier and is given as

$$CMRR|_{ACSFAFF} = \frac{A_{dm}}{A_{cm}} = 1 + 2(g_m + g_{mb})R_{Total}$$

4.4 Clock gated current mirror sense amplifier flipflop:

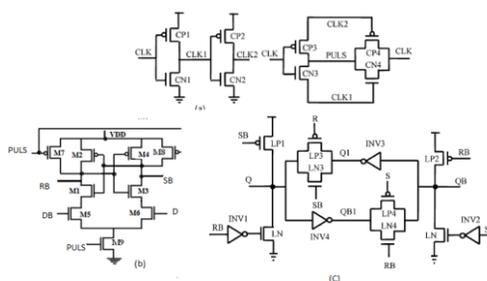


4.3 Clock gated current mirror sense amplifier

flipflop (a)Pulse generator stage (b)Sensing stage (c)Latching stage

In order to eliminate the redundant transitions in the pulse generator, the CG-SAFF is constructed. It utilizes the DETSAFF design as a baseline and incorporates the clock gating technique. In CG-SAFF, the clock gating technique is implemented by embedding a control circuit in the explicit pulse generator so that the PULS signal generation is disabled in a redundant event. The current mirror sense amplifier has better improvement in the noise immunity and speed of read circuit. Current Mirror Sense Amplifier takes differential input and amplify them large signal output. The differential approach presents numerous advantage over single ended counterpart – one of the most important being common mode rejection. That is such amplifier rejects the noise that is equally injected at both input. The signal common at both input suppressed at output of amplifier. Clock gated current mirror sense amplifier having three stages: pulse generator stage, sensing stage, latching stage. In pulse generator stage consist of 4 pmos & 4 nmos, totally 8 transistors. Sensing stage consists of 5 transistors. SB signal was taken in between CM5 & CM3 & RB signal was taken in between CM2 & CM4. latching stage consists of four nmos & four pmos. SB signal & PULS signal was taken from sensing stage.

4.5 Clock gated full latch sense amplifier flipflop:



4.4 Clock gated Full latch sense amplifier flipflop (a)Pulse generator stage (b)Sensing stage (c)Latching stage

The power problem is one of the most serious limitations in the high performance - VLSI's circuits. The power dissipation of on chip memories and interface circuits occupies a large portion of the total power dissipation. Full latch sense amplifier consumes less power than other configuration of sense amplifier. Even though the conventional latch based on two cross coupled inverters is widely used as a sense amplifier, it always requires some decoupling at its input. This drawback does not occur for the latch circuit shown in fig -3. The most critical point of latch-type sense amplifiers is that once the decision process has started, it does not recover unless the circuit is reset to the metastable. Due to fast speed, low power consumption, high input impedance and full-swing output latch type sense amplifier are very attractive for many applications. . Clock gated current mirror sense amplifier having three stages: pulse generator stage, sensing stage, latching stage. In pulse generator stage consist of 4 pmos & 4 nmos, totally 8 transistors. Sensing stage consists of 9 transistors. SB signal was taken in between CM5 & CM3 & RB

signal was taken in between CM2 & CM4.latching stage consists of four nmos& four pmos.SB signal & PULS signal was taken from sensing stage.

Comparison Table:

32nm Technology:

Types	Set time (ns)	Hold time(ns)	Delay (ns)	Power(W)	PDP
DET-SAFF	287	49	336	26.352u	8854.272
DSAFF-Ct mirror	162	42	204	30.040u	6128.16
DSAFF-Full latch	143	52	195	44.495u	8676.525

TABLE 4.1

At 32nm technology dual edge trigger current mirror sense amplifier consumes 30.040uW . Its less than that of dual edge triggered full latch sense amplifier and also power delay product of dual edge trigger current mirror sense amplifier is (6128.16) less than that of the dual edge trigger full latch (8676.525).

45nm Technology

Types	Set time (ns)	Hold time(ns)	Delay(ns)	Power(W)	PDP
DET-SAFF	217	32	249	24.857u	6189.393
DSAF F-Ct mirror	102	90	192	26.985u	5181.12
DSAF F-Full latch	12	45	57	36.956u	2106.49

TABLE 4.2

At 45nm technology dual edge trigger current mirror sense amplifier consumes 26.985uW . Its less than that of dual edge triggered full latch sense amplifier.

65nm Technology:

TABLE 4.3

Types	Set time (ns)	Hold time (ns)	Delay (ns)	Power (W)	PDP
DET-SAFF	65	31	96	1.494m	143.424
DSAF F-Ct mirror	26	66	92	2.227m	204.884
DSAF F-Full latch	128	10	138	3.042m	419.796

90nm Technology:

Types	Set time (ns)	Hold time (ns)	Delay (ns)	Power (W)	PDP
DSAF F-Ct mirror	16	56	72	0.323m	23.256
DSAF F-Full latch	112	42	154	0.457m	70.378
DET-SAFF	137	35	172	0.239m	41.108

TABLE 4.4

At 65nm technology dual edge trigger current mirror sense amplifier consumes 0.323mW. Its less than that of dual edge triggered full latch sense amplifier and also power delay product of dual edge trigger current mirror sense amplifier is (23.256)less than that of the dual edge trigger full latch (70.378).

At 90nm technology dual edge trigger current mirror sense amplifier consumes2.227mW. Its less than that of dual edge triggered full latch sense amplifier and also power delay product of dual edge trigger current mirror sense amplifier is (204.884) less than that of the dual edge trigger full latch (419.796).

MICROWIND

MICROWIND is truly integrated EDA software encompassing IC designs from concept to completion, enabling chip designers to design beyond their imagination. MICROWIND integrates traditionally separated front-end and back-end chip design into an integrated flow, accelerating the design cycle and reduced design

Complexities. It tightly integrates mixed-signal implementation with digital implementation, circuit simulation, transistor-level extraction and verification – providing an innovative education initiative to help individuals to develop the skills needed for design positions in virtually every domain of IC industry

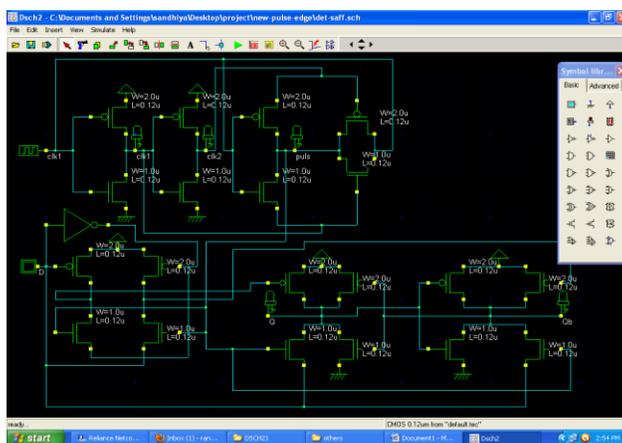
The present manual introduces the design and simulation of CMOS integrated circuits, in an attractive way thanks to user-friendly PC tools Dsch and Microwind 3.1. The DSCH program is a logic editor and simulator. DSCH is used to validate the architecture of the logic circuit before the microelectronics design is started. DSCH provides a user friendly environment for hierarchical logic design, and simulation with delay analysis, which allows the design and validation of complex logic structures. A key innovative feature is the possibility to estimate the power consumption of the circuit. Some techniques for low power design are described in the manual.

The MICROWIND 3.1 program allows the student to design and simulate an integrated circuit at physical description level. The package contains a library of common logic and analog ICs to view and simulate. MICROWIND 3.1 includes all the commands for a mask editor as well as original tools never gathered before in a single module (2D and 3D process view, VERILOG compiler, tutorial on MOS devices). We can gain access to Circuit Simulation by pressing one single key. The electric extraction of your circuit is automatically performed and the analog simulator produces voltage and current curves immediately. Simulation and output wave form

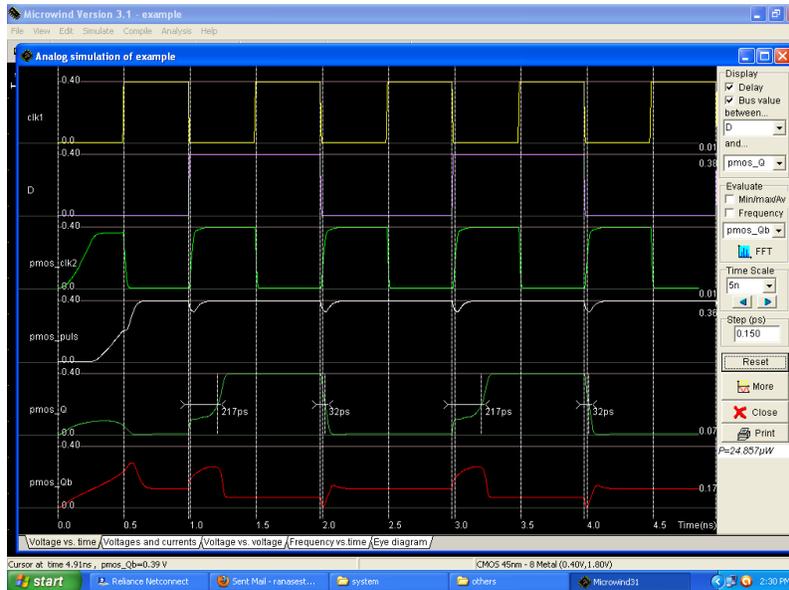
5.1DET-SAFF schematic diagram:

Simulation and output wave form

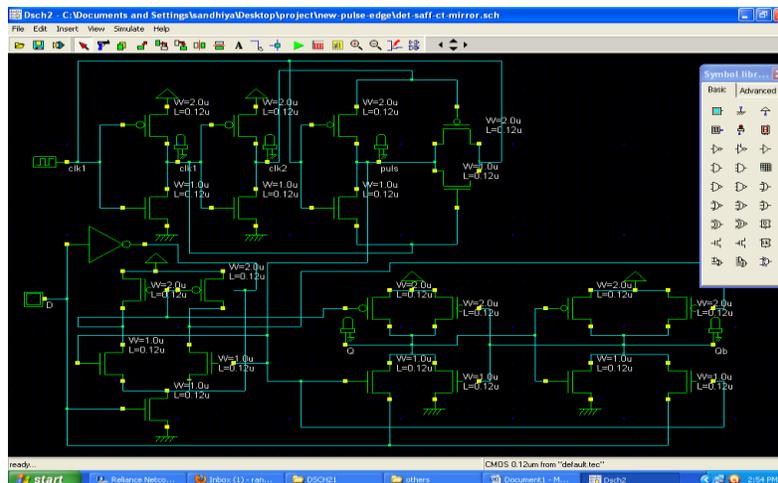
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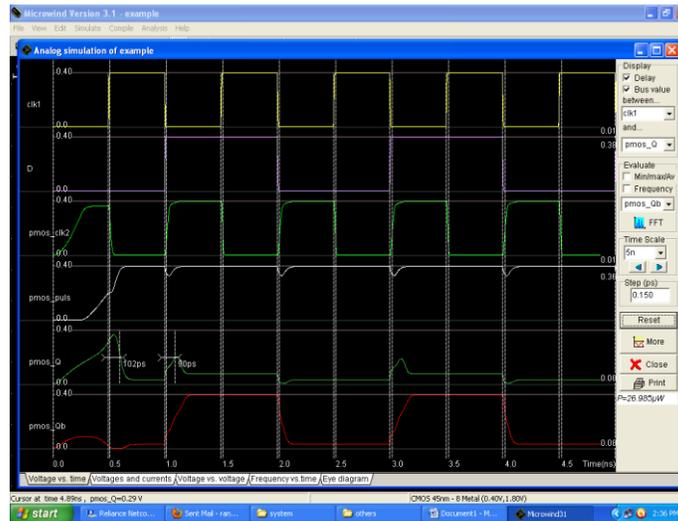
5.2DET-SAFF output diagram:



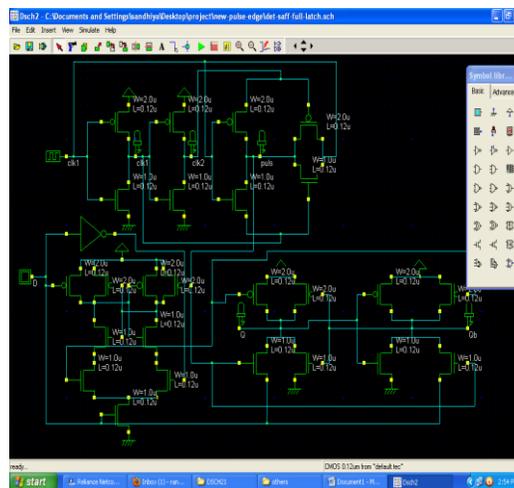
5DET-current mirror schematic diagram



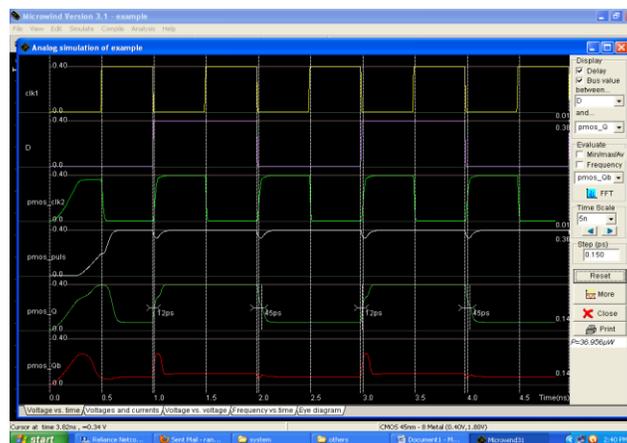
6DET-current mirror output diagram



5.7DET-full latch schematic diagram:



5.8DET-full latch output diagram



CONCLUSION

This project presents four types of dual edge triggered sense amplifier flipflop by using current mirror sense amplifier circuit and full latch sense amplifier circuit such as double edge triggered sense amplifier flip flop using current mirror , double edge triggered sense amplifier flip flop using full latch and clock gated sense amplifier flip flop using current mirror, clock gated sense amplifier flipflop using full latch. According to the power and PDP analysis the dual edge trigger current mirror sense amplifier is superior to dual edge triggered full latch sense amplifier. At 45nm technology the dual edge trigger current mirror sense amplifier consumes 26.985uW. At 45nm technology the clock gated current mirror sense amplifier consumes 3.788uW.

It is concluded that the dual edge trigger current mirror sense amplifier flipflop is suitable to design the VLSI clocking system with high switching activity and the clock gated current mirror sense amplifier flipflop is suitable to design the VLSI clocking system with low switching activity.

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